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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I²C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	81
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401vct6

Contents

3.14 Power supply supervisor

3.14.1 Internal reset ON

This feature is available for V_{DD} operating voltage range 1.8 V to 3.6 V.

The internal power supply supervisor is enabled by holding PDR_ON high.

The devices have an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR is always active, and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes.

The devices remain in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR}, without the need for an external reset circuit.

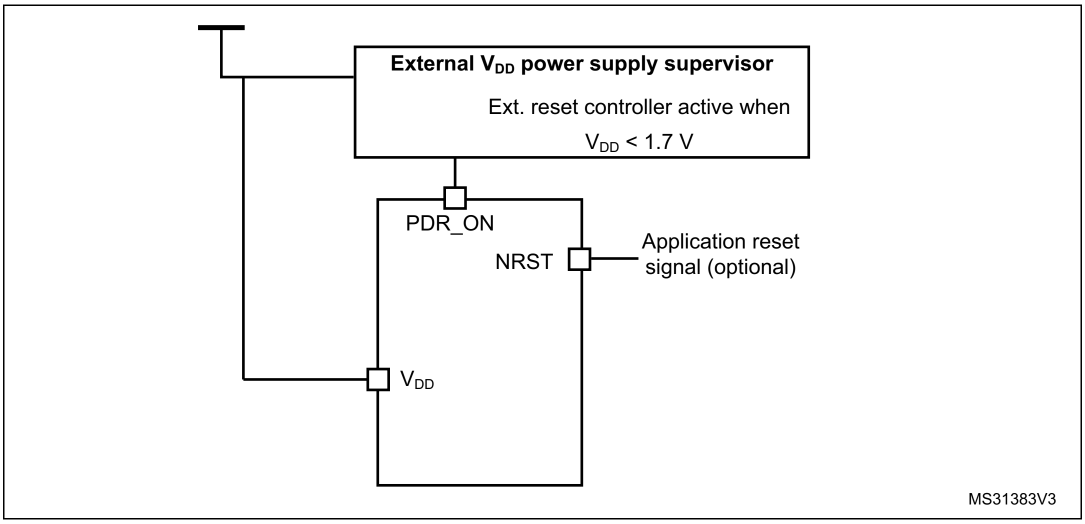
The devices also feature an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.14.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled by setting the PDR_ON pin to low.

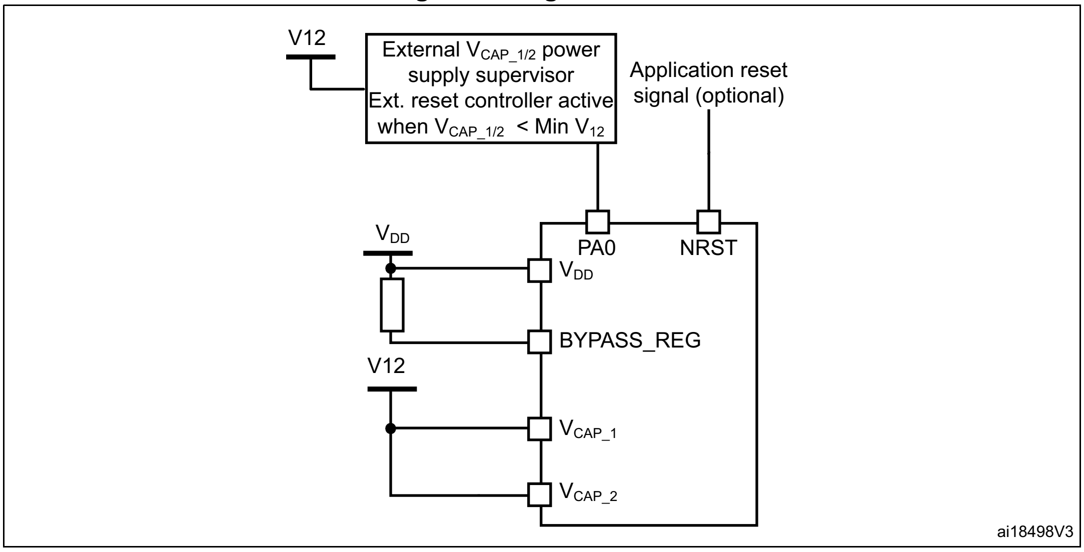
An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to *Figure 5: Power supply supervisor interconnection with internal reset OFF*.

Figure 5. Power supply supervisor interconnection with internal reset OFF(1)



1. The PRD_ON pin is only available on the WLCSP49 and UFBGA100 packages.

Figure 7. Regulator OFF



The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see *Figure 8*).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see *Figure 9*).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application

3.15.3 Regulator ON/OFF and internal power supply supervisor availability

Table 3. Regulator ON/OFF and internal power supply supervisor availability

Package	Regulator ON	Regulator OFF	Power supply supervisor ON	Power supply supervisor OFF
UFQFPN48	Yes	No	Yes	No
WLCSP49	Yes	No	Yes PDR_ON set to VDD	Yes PDR_ON external control(1)
LQFP64	Yes	No	Yes	No
LQFP100	Yes	No	Yes	No
UFBGA100	Yes BYPASS_REG set to VSS	Yes BYPASS_REG set to VDD	Yes PDR_ON set to VDD	Yes PDR_ON external control (1)

1. Refer to *Section 3.14: Power supply supervisor*

3.16 Real-time clock (RTC) and backup registers

The backup domain includes:

- The real-time clock (RTC)
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC features a reference clock detection, a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 µs to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see *Section 3.17: Low-power modes*).

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

The RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.17 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

  The devices can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm/ wakeup/ tamper/ time stamp events).

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain when selected.

  The devices exit the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm/ wakeup/ tamper/time stamp event occurs.

  Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

3.18 V_{BAT} operation

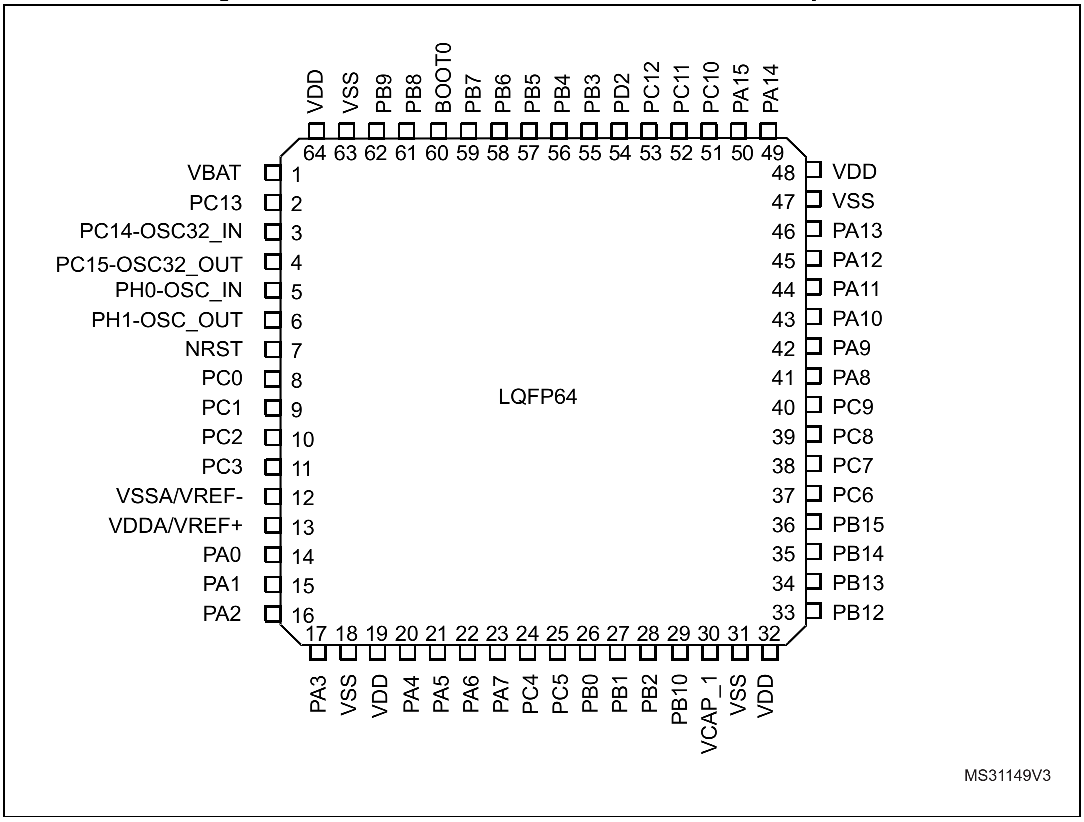
The VBAT pin allows to power the device V_{BAT} domain from an external battery, an external super-capacitor, or from V_{DD} when no external battery and an external super-capacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The VBAT pin supplies the RTC and the backup registers.

Note: When the microcontroller is supplied from VBAT, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation. When PDR_ON pin is not connected to V_{DD} (internal Reset OFF), the V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD}.

Figure 12. STM32F401xB/STM32F401xC LQFP64 pinout



1. The above figure shows the package top view.

Table 10. STM32F401xB/STM32F401xC register boundary addresses (continued)

Bus	Boundary address	Peripheral
APB2	0x4001 4C00- 0x4001 FFFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4/I2S4
	0x4001 3000 - 0x4001 33FF	SPI1
	0x4001 2C00 - 0x4001 2FFF	SDIO
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1
	0x4001 1800 - 0x4001 1FFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
	0x4001 0000 - 0x4001 03FF	TIM1
	0x4000 7400 - 0x4000 FFFF	Reserved

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD_x} power lines (source)(1)	160	mA
ΣI_{VSS}	Total current out of sum of all V_{SS_x} ground lines (sink)(1)	-160	
I_{VDD}	Maximum current into each V_{DD_x} power line (source)(1)	100	
I_{VSS}	Maximum current out of each V_{SS_x} ground line (sink)(1)	-100	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/O and control pin	-25	
ΣI_{IO}	Total output current sunk by sum of all I/O and control pins (2)	120	
	Total output current sourced by sum of all I/Os and control pins(2)	-120	
$I_{INJ(PIN)}$ (3)	Injected current on FT pins (4)	–5/+0	
	Injected current on NRST and B pins (4)		
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Negative injection disturbs the analog performance of the device. See note in *Section 6.3.20: 12-bit ADC characteristics*.
4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	125	
T_{LEAD}	Maximum lead temperature during soldering (WLCSP49, LQFP64/100, UFQFPN48, UFBGA100)	see note (1)	

1. Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK® 7191395 specification, and the European directive on Restrictions on Hazardous Substances (ROHS directive 2011/65/EU, July 2011).

Table 21. Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A= 25 °C	T_A=85 °C	T_A=105 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(2)(3)	84	20.2	21	22	23	mA
			60	14.7	15	16	18	
			40	10.7	11	12	13	
			20	5.7	6	7	8	
		External clock, all peripherals disabled(3)	84	11.2	12	13	14	
			60	8.2	9	10	11	
			40	6.1	7	8	9	
			20	3.4	4	5	6	

1. Guaranteed by characterization, unless otherwise specified.
2. When analog peripheral blocks such as ADC, HSE, LSE, HSI, or LSI are ON, an additional power consumption has to be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.

Table 22. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory- V_{DD} = 1.8 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(2)(3)	84	22.2	**23**	24	25	mA
			60	14.5	15	16	17	
			40	10.7	11	12	13	
			30	8.6	9	10	11	
			20	7.0	8	9	10	
		External clock, all peripherals disabled(3)	84	11.5	12	13	14	
			60	7.7	8	9	10	
			40	5.6	6	7	8	
			30	4.5	5	6	7	
			20	3.8	5	6	7	

1. Guaranteed by characterization, unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 23. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory - V_{DD} = 3.3 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(2)(3)	84	22.5	**23**	24	25	mA
			60	14.8	16	17	18	
			40	11.0	12	13	14	
			30	8.9	10	11	12	
			20	7.3	8	9	10	
		External clock, all peripherals disabled(3)	84	11.8	13	14	15	
			60	7.9	9	10	11	
			40	5.8	7	8	9	
			30	4.8	6	7	8	
			20	4.0	5	6	7	

1. Guaranteed by characterization, unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

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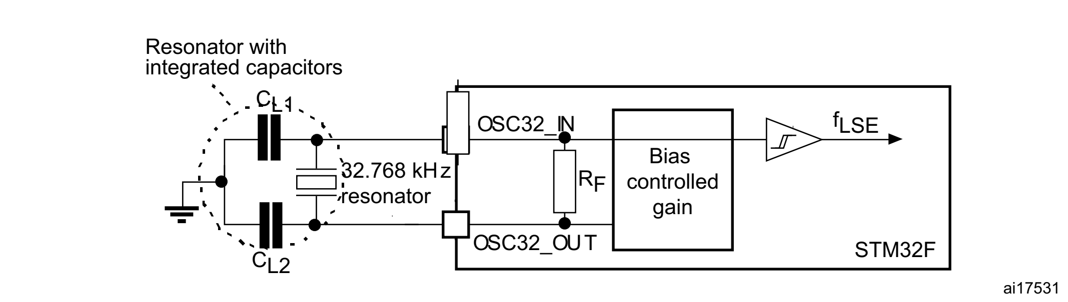
Table 24. Typical and maximum current consumption in run mode, code with data processing (ART accelerator disabled) running from Flash memory

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, all peripherals enabled(2)(3)	84	30.6	32	34	35	mA
			60	21.4	22	24	25	
			40	15.6	16	17	18	
			30	12.7	13	14	15	
			20	10.0	11	12	13	
		External clock, all peripherals disabled(3)	84	19.9	21	23	25	
			60	14.6	15	16	17	
			40	10.4	11	12	13	
			30	8.6	9	10	11	
			20	6.7	7	8	9	

1. Guaranteed by characterization, unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Figure 25. Typical application with a 32.768 kHz crystal



6.3.9 Internal clock source characteristics

The parameters given in *Table 39* and *Table 40* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

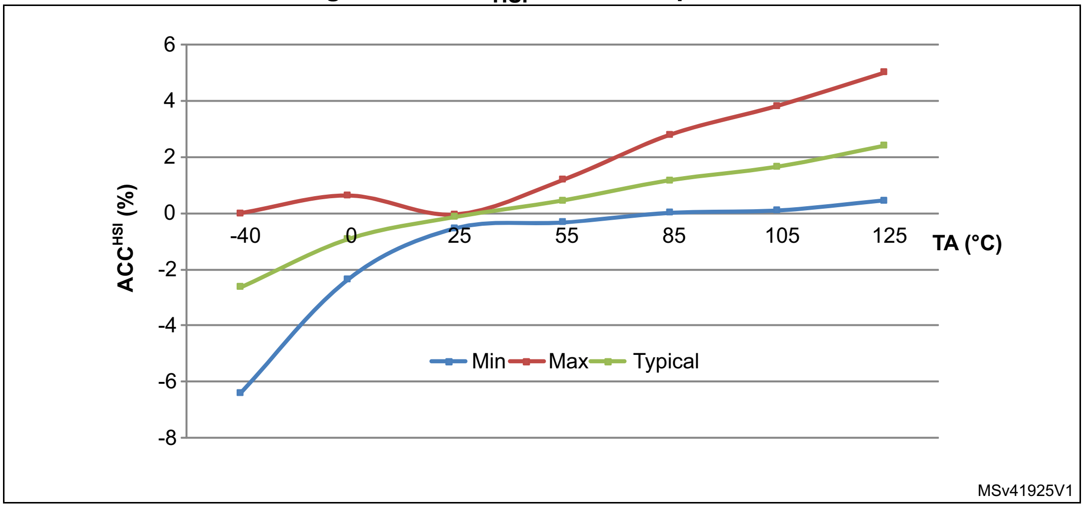
High-speed internal (HSI) RC oscillator

Table 39. HSI oscillator characteristics (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user trimming step(2)	-	-	-	1	%
	Accuracy of the HSI oscillator	T_A = –40 to 105 °C(3)	–8	-	4.5	%
		T_A = –10 to 85 °C(3)	–4	-	4	%
		T_A = 25 °C(4)	–1	-	1	%
$t_{su(HSI)}$(2)	HSI oscillator startup time	-	-	2.2	4	µs
$I_{DD(HSI)}$(2)	HSI oscillator power consumption	-	-	60	80	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design.
3. Guaranteed by characterization.
4. Factory calibrated, parts not soldered.

Figure 26. ACC_{HSI} versus temperature



1. Guaranteed by characterization.

Low-speed internal (LSI) RC oscillator

Table 40. LSI oscillator characteristics [(1)]

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}[(2)]	Frequency	17	32	47	kHz
$t_{su(LSI)}$[(3)]	LSI oscillator startup time	-	15	40	µs
$I_{DD(LSI)}$[(3)]	LSI oscillator power consumption	-	0.4	0.6	µA

1. V_{DD} = 3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by characterization.
3. Guaranteed by design.

6.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 49: EMI characteristics for WLCSP49*). It is available only on the main PLL.

Table 43. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max(1)	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP		-	-	2^{15}-1	-

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = round[f_{PLL\_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If f_{PLL_IN} = 1 MHz, and f_{MOD} = 1 kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = round[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = round[((2^{15} - 1) \times md \times PLLN) / (100 \times 5 \times MODEPER)]$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = round[((2^{15} - 1) \times 2 \times 240) / (100 \times 5 \times 250)] = 126md(quantitazed)\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{quantized}\% = (MODEPER \times INCSTEP \times 100 \times 5) / ((2^{15} - 1) \times PLLN)$$

As a result:

$$md_{quantized}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.002\%(peak)$$

Table 45. Flash memory programming

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	300	600	
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1200	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	700	1400	
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	4	8	s
		Program/erase parallelism (PSIZE) = x 16	-	2.75	5.5	
		Program/erase parallelism (PSIZE) = x 32	-	2	4	
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3.6	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization.
2. The maximum programming time is measured after 100K erase operations.

Table 46. Flash memory programming with V_{PP} voltage

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Double word programming	T_A = 0 to +40 °C V_{DD} = 3.3 V V_{PP} = 8.5 V	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	1.750	-	s

Table 66. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{lat}[2]	Injection trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.100	µs
			-	-	3[5]	$1/f_{ADC}$
t_{latr}[2]	Regular trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.067	µs
			-	-	2[5]	$1/f_{ADC}$
t_S[2]	Sampling time	f_{ADC} = 30 MHz	0.100	-	16	µs
			3	-	480	$1/f_{ADC}$
t_{STAB}[2]	Power-up time		-	2	3	µs
t_{CONV}[2]	Total conversion time (including sampling time)	f_{ADC} = 30 MHz 12-bit resolution	0.50	-	16.40	µs
		f_{ADC} = 30 MHz 10-bit resolution	0.43	-	16.34	µs
		f_{ADC} = 30 MHz 8-bit resolution	0.37	-	16.27	µs
		f_{ADC} = 30 MHz 6-bit resolution	0.30	-	16.20	µs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$
f_S[2]	Sampling rate (f_{ADC} = 30 MHz, and t_S = 3 ADC cycles)	12-bit resolution Single ADC	-	-	2	Msps
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msps
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msps
I_{VREF+}[2]	ADC V_{REF} DC current consumption in conversion mode		-	300	500	µA
I_{VDDA}[2]	ADC V_{DDA} DC current consumption in conversion mode		-	1.6	1.8	mA

1. V_{DDA} minimum value of 1.7 V is possible with the use of an external power supply supervisor (refer to *Section 3.14.2: Internal reset OFF*).
2. Guaranteed by characterization.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA}.
4. R_{ADC} maximum value is given for V_{DD}=1.7 V, and minimum value for V_{DD}=3.3 V.
5. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 66*.

Table 70. ADC dynamic accuracy at f_{ADC} = 18 MHz - limited test conditions[1]

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	f_{ADC} =18 MHz V_{DDA} = V_{REF+}= 1.7 V Input Frequency = 20 KHz Temperature = 25 °C	10.3	10.4	-	bits
SINAD	Signal-to-noise and distortion ratio		64	64.2	-	dB
SNR	Signal-to-noise ratio		64	65	-	
THD	Total harmonic distortion		-67	-72	-	

1. Guaranteed by characterization.

Table 71. ADC dynamic accuracy at f_{ADC} = 36 MHz - limited test conditions[1]

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	f_{ADC} = 36 MHz V_{DDA} = V_{REF+} = 3.3 V Input Frequency = 20 KHz Temperature = 25 °C	10.6	10.8	-	bits
SINAD	Signal-to noise and distortion ratio		66	67	-	dB
SNR	Signal-to noise ratio		64	68	-	
THD	Total harmonic distortion		-70	-72	-	

1. Guaranteed by characterization.

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.16* does not affect the ADC accuracy.

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output characteristics.

Figure 44. SDIO high-speed mode

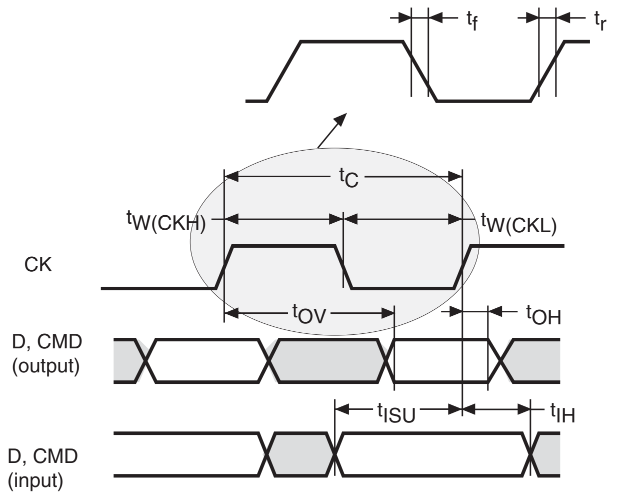


Figure 45. SD default mode

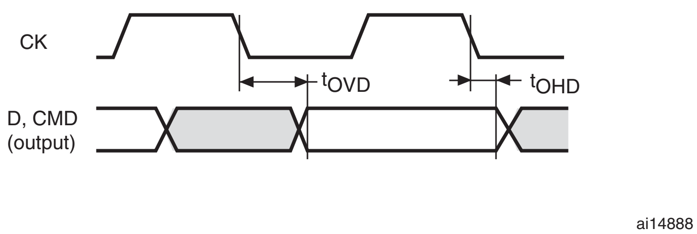


Table 77. Dynamic characteristics: SD / MMC characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode		0	-	48	MHz
-	SDIO_CK/fPCLK2 frequency ratio		-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp = 48MHz	8.5	9	-	ns
$t_{W(CKH)}$	Clock high time	fpp = 48MHz	8.3	10	-	
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	fpp = 48MHz	3.5	-	-	ns
t_{IH}	Input hold time HS	fpp = 48MHz	0	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	fpp = 48MHz	-	4.5	7	ns
t_{OH}	Output hold time HS	fpp = 48MHz	3	-	-	

Table 80. WLCSP49 recommended PCB design rules (0.4 mm pitch)

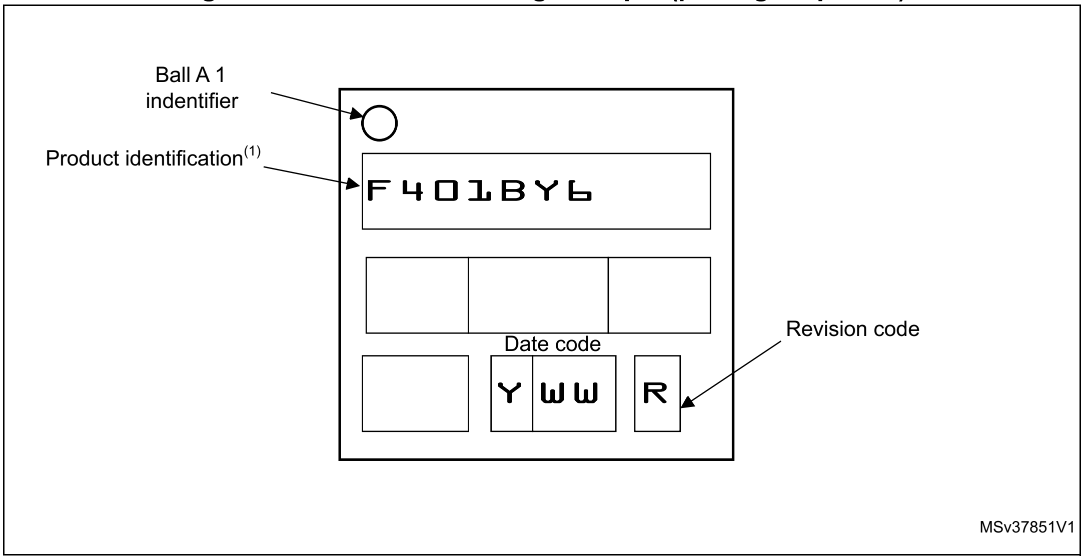
Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed

WLCSP49 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 48. WLCSP49 marking example (package top view)



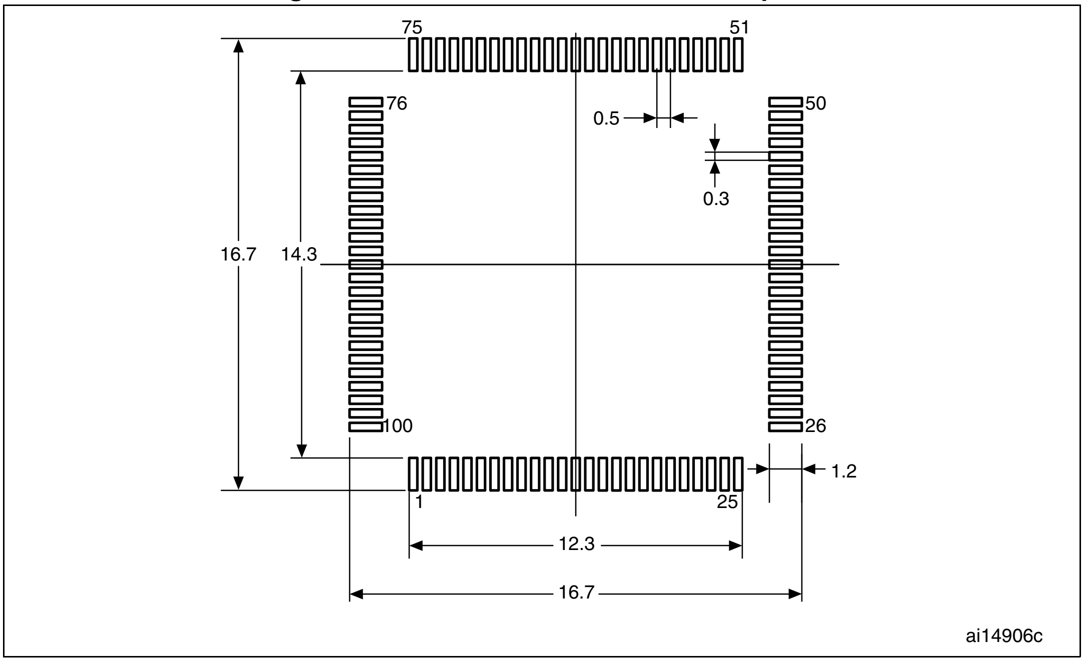
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 83. LQPF100- 100-pin, 14 x 14 mm, 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[(1)]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.60	-	-	0.063
A1	0.050	-	0.150	0.002	-	0.0059
A2	1.350	1.40	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.622	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.622	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
K	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	0.080			0.0031		

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 56. LQFP100 recommended footprint



1. Dimensions are in millimeters.